

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	2	((("5278439") or ("6723604"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/08/17 08:26
S1	718	(257/390).CCLS.	USPAT; USOCR	OR	OFF	2005/08/11 07:47
S2	1	("6415335").PN.	USPAT; USOCR	OR	OFF	2005/08/09 12:40
S3	888	(257/390).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/08/09 14:28
S4	42	S3 and "select gate"	US-PGPUB; USPAT	OR	OFF	2005/08/09 14:29
S5	28	("5204286" "5254217" "5279982" "5323048" "5371030" "5397726" "5442236" "5519239" "5654577" "5705419" "5710462" "5717251" "5734187" "5918124" "6080624").PN. OR ("6160297" "6674132").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/09 15:02
S6	1	("5969383").PN.	USPAT; USOCR	OR	OFF	2005/08/09 15:43
S7	373863	select gate with oxide with (depth or thickness or thick)	USPAT	OR	OFF	2005/08/09 15:44
S8	106	"select gate" with oxide with (depth or thickness or thick)	USPAT	OR	OFF	2005/08/09 15:44
S10	3830	((257/E27.103) or (257/E21.68)). CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 07:45
S11	460	S10 and "select gate"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 07:45
S12	428	S10 and "select gate" and "control gate"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:41
S13	208	S10 and "select gate" and "control gate" and "silicon nitride" and "polysilicon"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 07:46

S14	133	S10 and "select gate" and "control gate" and "silicon nitride" and "polysilicon" and "silicon oxide"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 07:46
S15	133	S10 and "select gate" and "control gate" and "silicon nitride" and "polysilicon" and "silicon oxide" and (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 08:52
S16	32	hsieh and split-gate	US-PGPUB	OR	OFF	2005/08/10 09:01
S17	219	hsieh and flash	US-PGPUB	OR	OFF	2005/08/10 09:01
S18	6	hsieh and flash and "select gate"	US-PGPUB	OR	OFF	2005/08/10 09:02
S19	1	("6674132").PN.	USPAT; USOCR	OR	OFF	2005/08/10 11:55
S20	1	("6160297").PN.	USPAT; USOCR	OR	OFF	2005/08/10 11:55
S21	12	("4814286" "5789296" "5872036" "5930631" "6001690" "6069042" "6071777" "6091104" "6194272" "6232185").PN. OR ("6387757").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/10 14:09
S22	3830	((257/E27.103) or (257/E21.68)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 14:42
S23	55	S22 and "select gate" and "control gate" and ("memory layer" or (trap\$4 near5 charge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/11 08:42
S24	117	S22 and "select gate" and (thick\$5 with nm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/10 15:11
S36	2	harari and "20040165443"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/11 08:44
S37	2	hsu and "20030227047"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/11 08:45

S38	14	shimizu and "6160297"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/11 08:46
S43	101	("5020030" "5051793" "5063172" "5130769" "5225362" "5274588" "5280446").PN. OR ("5408115").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/11 10:03
S44	24	S43 and "select gate"	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/11 10:23
S45	1	("6674132").PN.	USPAT; USOCR	OR	OFF	2005/08/11 12:17
S46	26	"select gate" and "control gate" and "polysilicon" and "memory cell row"	USPAT	OR	OFF	2005/08/11 12:32
S47	22	(("select gate" with "control gates") with between) and "polysilicon" and "memory"	USPAT	OR	OFF	2005/08/11 12:49
S48	47	(("select gate" with "control gates") with (adjacent or "next to" or between)) and "polysilicon" and "memory"	US-PGPUB; USPAT	OR	OFF	2005/08/11 12:49
S49	25	S48 and (not S47) and (not "I26")	US-PGPUB; USPAT	OR	OFF	2005/08/11 13:11
S50	1088	hsieh and flash	US-PGPUB; USPAT	OR	OFF	2005/08/11 13:11
S51	58	hsieh and flash and "select gate"	US-PGPUB; USPAT	OR	OFF	2005/08/11 14:18
S53	10	"chen, wei-ming" and "split gate" and "memory"	US-PGPUB; USPAT	OR	OFF	2005/08/11 14:18
S54	3166	(257/314,316,321,324).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/08/15 10:19
S55	328	S54 and "select gate"	US-PGPUB; USPAT	OR	OFF	2005/08/15 10:19
S56	211	toshiba and nand and memory and @ad<"19900101"	US-PGPUB; USPAT	OR	OFF	2005/08/15 13:15
S57	9	S56 and flash	US-PGPUB; USPAT	OR	OFF	2005/08/15 12:29
S58	3166	(257/314,316,321,324).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/08/15 13:15
S60	18	S58 and ((select adj gate) or (program adj gate)) and (@pd<"20030407") and NAND and (ono or sonos or (nitride near6 oxide) near silicon) and (sidewall or spacer)	US-PGPUB; USPAT	OR	OFF	2005/08/15 15:04

S62	3166	(257/314,316,321,324).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/08/15 15:05
S63	109	S62 and ((select adj gate) or (program adj gate)) and (@pd<"20030407") and (sidewall or spacer)	US-PGPUB; USPAT	OR	OFF	2005/08/15 16:26
S64	1	("5969383").PN.	US-PGPUB; USPAT	OR	OFF	2005/08/15 16:26
S65	2	("2003/0006450").URPN.	USPAT	OR	OFF	2005/08/16 08:24
S66	4531	NAND, memory, flash,	USPAT	AND	OFF	2005/08/16 08:25
S67	457	NAND, memory, flash, ONO	USPAT	AND	OFF	2005/08/16 08:25
S68	160	NAND, memory, flash, ONO, "select gate"	USPAT	AND	OFF	2005/08/16 08:25
S69	156	NAND, memory, flash, ONO, "select gate", "control gate"	USPAT	AND	OFF	2005/08/16 08:25
S70	57	NAND, memory, flash, ONO, "select gate", "control gate", "silicon oxide", "silicon nitride"	USPAT	AND	OFF	2005/08/16 13:36
S71	93	("select gate" near5 ("dielectric" or "oxide")) near5 (thick\$5 or angstrom or nm)	USPAT	AND	OFF	2005/08/16 13:50
S72	0	hsieh, memory, nand	JPO	AND	OFF	2005/08/16 13:50
S74	222	hsieh	JPO	AND	OFF	2005/08/16 13:52
S79	176	hsieh, flash	EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/08/16 13:54
S82	157	hsieh, flash, memory	EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/08/16 13:54
S83	9	hsieh, flash, memory, select	EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/08/16 14:07
S84	27	hsieh, memory, select	EPO; JPO; DERWENT; IBM_TDB	AND	OFF	2005/08/16 14:16
S85	923	hsieh, memory, select	USPAT	AND	OFF	2005/08/16 14:16
S86	184	hsieh, memory, select, nand	USPAT	AND	OFF	2005/08/16 14:16
S87	1	("6645813").PN.	US-PGPUB; USPAT	OR	OFF	2005/08/16 14:16
S88	13	("5278439" "5429971" "5600166" "5677872" "5706227" "5712179" "6028336" "6151248" "6222762" "6255698" "6417036" "6538277").PN. OR ("6645813").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/16 14:20

S89	3323	438/257	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/16 14:20
S90	1943	(438/257).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/08/16 14:21
S91	166	S90 and "select gate"	US-PGPUB; USPAT	OR	OFF	2005/08/16 14:49
S92	355	nand and "select gate" and memory and "control gate" and ((oxide near5 nitride) or ("ONO" or "sonos" or "monos"))	US-PGPUB; USPAT	OR	OFF	2005/08/16 14:50
S93	184	nand and "select gate" and memory and "control gate" and ((oxide near5 nitride) or ("ONO" or "sonos" or "monos")) and "gate oxide"	US-PGPUB; USPAT	OR	OFF	2005/08/16 15:05
S94	2	10/282747	US-PGPUB; USPAT	OR	OFF	2005/08/16 15:26
S95	1	("5824584").PN.	US-PGPUB; USPAT	OR	OFF	2005/08/17 08:26